

# GT60N321

High Power Switching Applications  
The 4th Generation

Unit: mm

- FRD included between emitter and collector
- Enhancement-mode
- High speed IGBT :  $t_f = 0.25 \mu s$  (typ.) ( $I_C = 60 A$ )  
FRD :  $t_{rr} = 0.8 \mu s$  (typ.) ( $di/dt = -20 A/\mu s$ )
- Low saturation voltage:  $V_{CE(sat)} = 2.3 V$  (typ.) ( $I_C = 60 A$ )

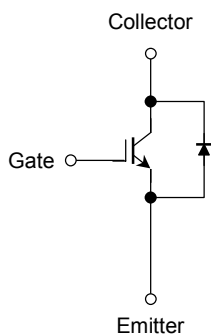
## Maximum Ratings (Ta = 25°C)

Characteristics	symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CES}$	1000	V
Gate-Emitter Voltage	$V_{GES}$	$\pm 25$	V
Collector Current	DC	$I_C$	A
	1 ms	$I_{CP}$	
Emitter-Collector Forward Current	DC	$I_{ECF}$	A
	1 ms	$I_{ECFP}$	
Collector Power Dissipation (Tc = 25°C)	$P_C$	170	W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~150	°C
Screw Torque	—	0.8	N·m



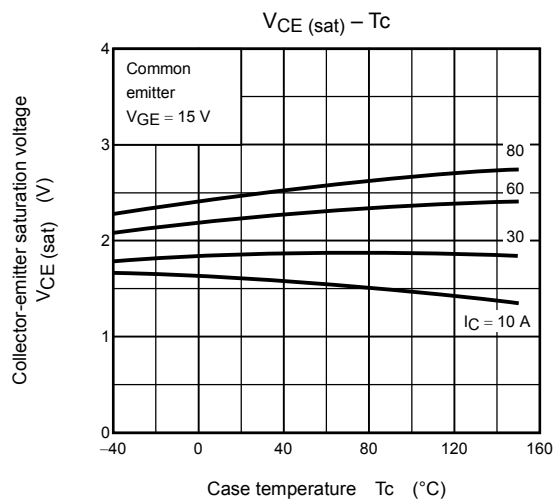
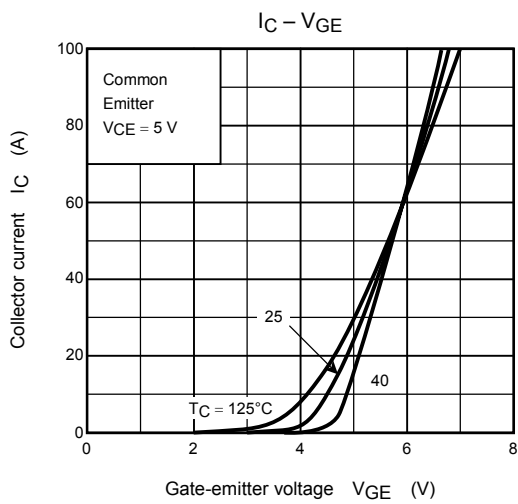
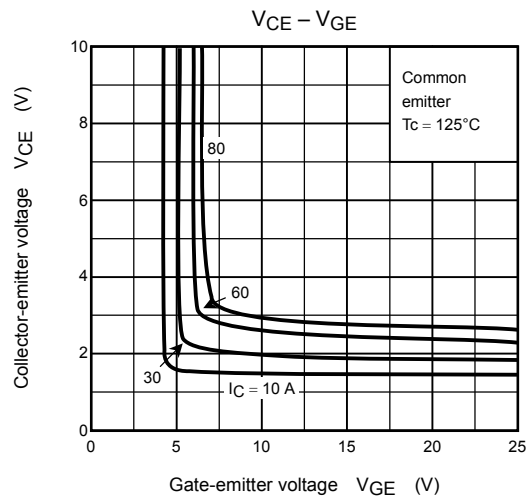
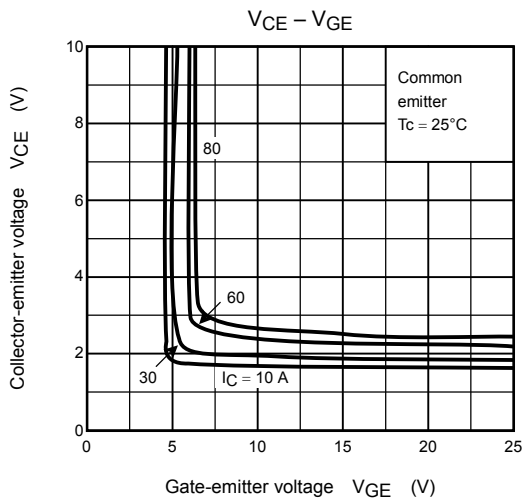
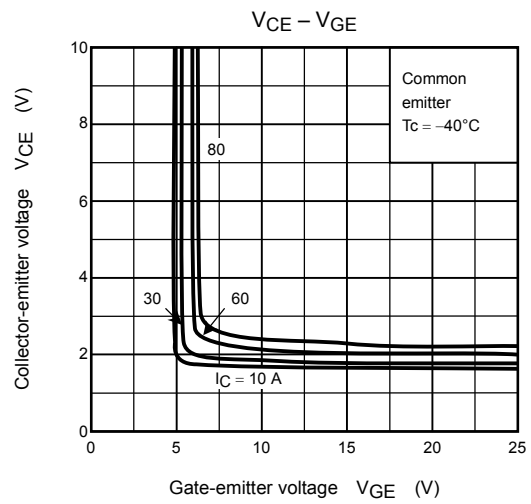
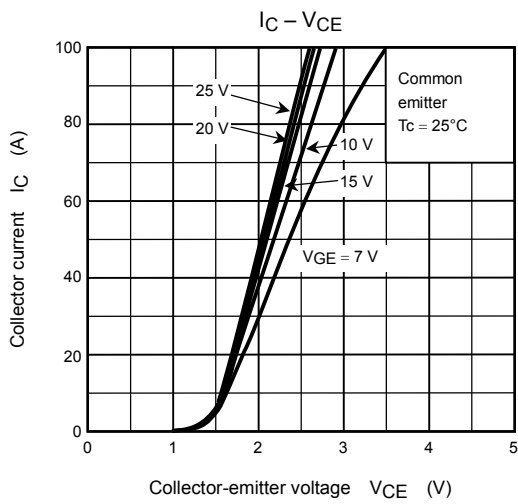
Weight: 9.75 g (typ.)

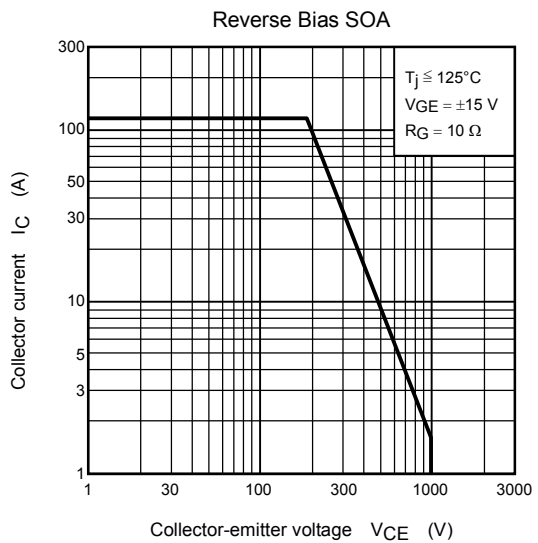
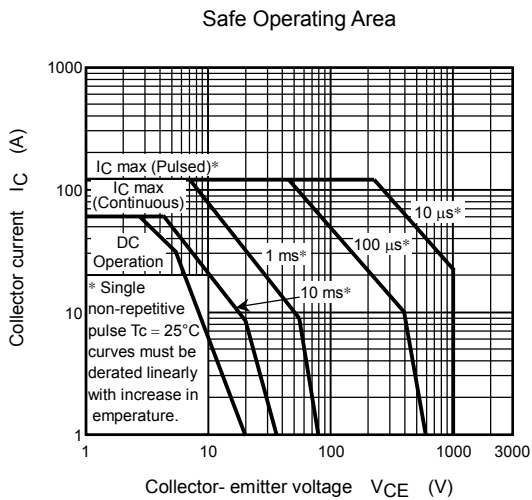
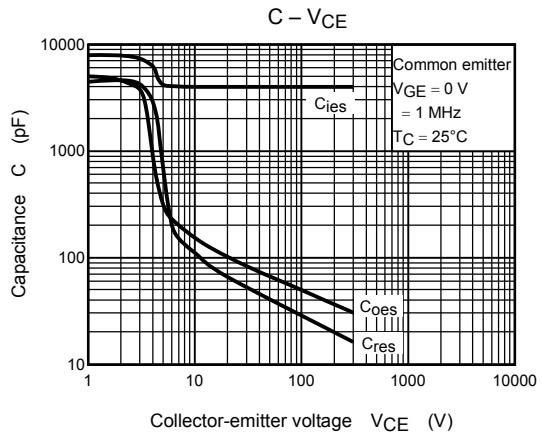
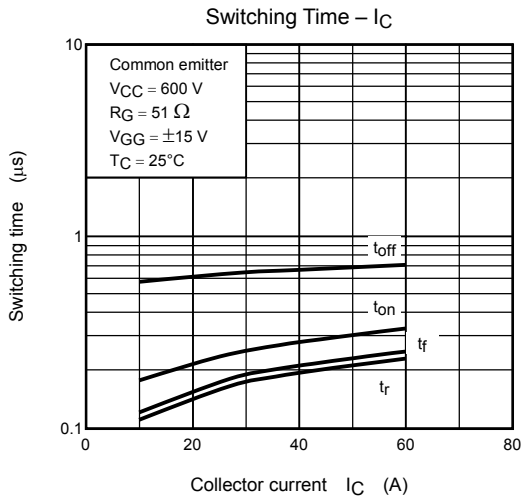
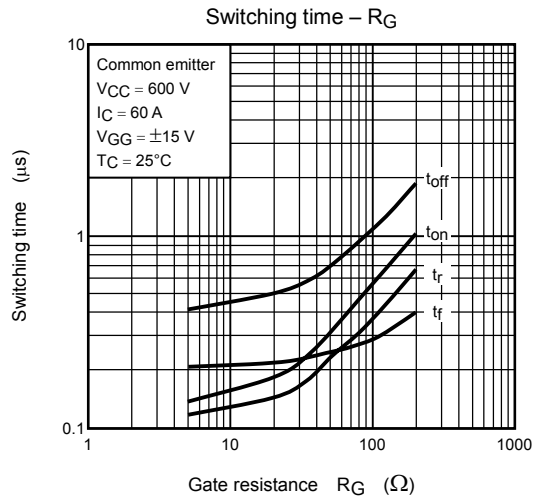
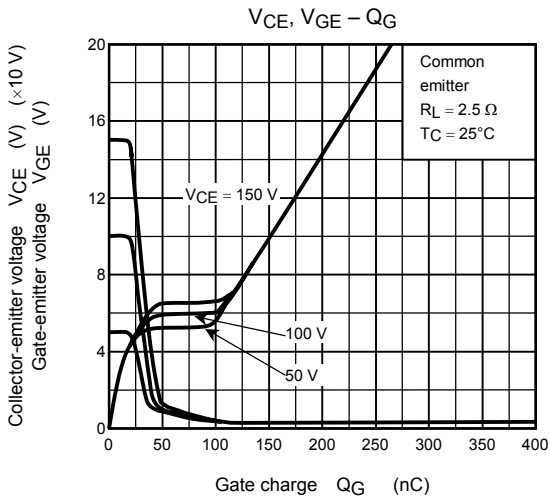
## Equivalent Circuit

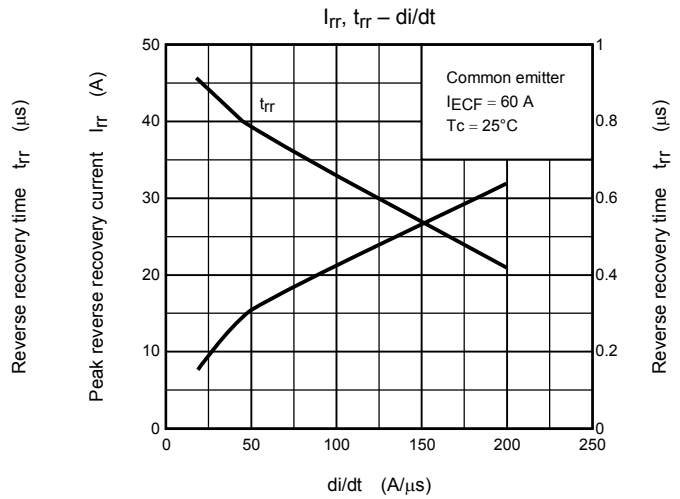
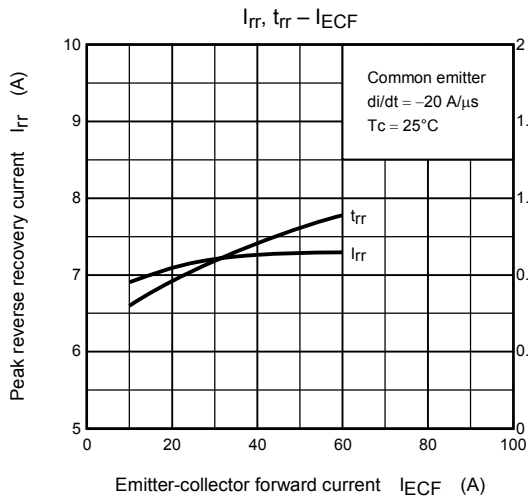
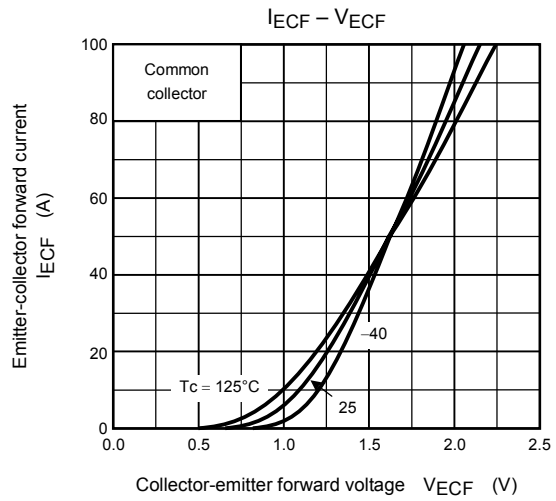
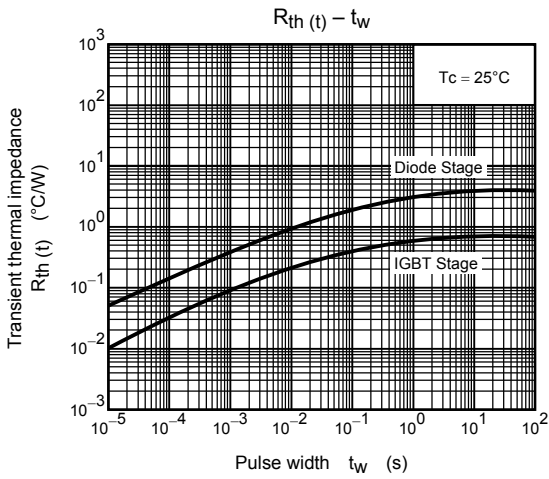


## Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate Leakage Current		$I_{GES}$	$V_{GE} = \pm 25 \text{ V}, V_{CE} = 0$	—	—	$\pm 500$	nA
Collector Cut-off Current		$I_{CES}$	$V_{CE} = 1000 \text{ V}, V_{GE} = 0$	—	—	1.0	mA
Gate-Emitter Cut-off Voltage		$V_{GE} \text{ (OFF)}$	$I_C = 60 \text{ mA}, V_{CE} = 5 \text{ V}$	3.0	—	6.0	V
Collector-Emitter Saturation Voltage		$V_{CE} \text{ (sat) (1)}$	$I_C = 10 \text{ A}, V_{GE} = 15 \text{ V}$	—	1.6	2.3	V
Collector-Emitter Saturation Voltage		$V_{CE} \text{ (sat) (2)}$	$I_C = 60 \text{ A}, V_{GE} = 15 \text{ V}$	—	2.3	2.8	V
Input Capacitance		$C_{ies}$	$V_{CE} = 10 \text{ V}, V_{GE} = 0, f = 1 \text{ MHz}$	—	4000	—	pF
Switching Time	Rise Time	$t_r$		—	0.23	—	μs
	Turn-on Time	$t_{on}$		—	0.33	—	
	Fall Time	$t_f$		—	0.25	0.40	
	Turn-off Time	$t_{off}$		—	0.70	—	
Emitter-Collector Forward Voltage		$V_{ECF}$	$I_{EC} = 15 \text{ A}, V_{GE} = 0$	—	1.5	2.0	V
Reverse Recovery Time		$t_{rr}$	$I_F = 15 \text{ A}, V_{GE} = 0, di/dt = -20 \text{ A}/\mu\text{s}$	—	0.8	2.5	μs
Thermal Resistance		$R_{h(j-c)}$	—	—	—	0.74	°C/W
Thermal Resistance		$R_{h(j-c)}$	—	—	—	4.0	°C/W







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